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With the principle of "Quality Parts, Customers Priority, Honest Operation, and Considerate Service", our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip, ALPS, ROHM, Xilinx, Pulse, ON, Everlight and Freescale. Main products comprise IC, Modules, Potentiometer, IC Socket, Relay, Connector. Our parts cover such applications as commercial, industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!



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CHIP MONOLITHIC CERAMIC CAPACITOR FOR AUTOMOTIVE GCM32EC71H106KA03_ (1210, X7S, 10uF, 50Vdc)

_: packaging code

Reference Sheet

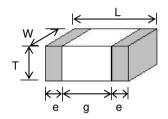
1.Scope

This product specification is applied to Chip Monolithic Ceramic Capacitor used for Automotive Electronic equipment.

2.MURATA Part NO. System

(Ex.)	GCM	32	E	C7	1H	106	K	A03	L
		(1)L/W Dimensions	(2)T Dimensions	(3)Temperature Characteristics	(4)DC Rated Voltage	(5)Nominal Capacitance	(6)Capacitance Tolerance	(7)Murata's Control Code	(8)Packaging Code

3. Type & Dimensions



(Unit:mm)

(1)-1 L	(1)-2 W	(2) T	е	g
3.2±0.3	2.5±0.2	2.5±0.2	0.3 min.	1.0 min.

4.Rated value

\ /	e Characteristics ode):X7S(EIA)	(4) DC Rated	(5) Nominal	(6) Capacitance	Specifications and Test Methods
Temp. coeff or Cap. Change	Temp. Range (Ref.Temp.)	Voltage	Capacitance	Tolerance	(Operationg Temp. Range)
-22 to 22 %	-55 to 125 °C (25 °C)	50 Vdc	10 uF	±10 %	-55 to 125 °C

5.Package

mark	(8) Packaging	Packaging Unit
L	φ180mm Reel EMBOSSED W8P4	1000 pcs./Reel
K	φ330mm Reel EMBOSSED W8P4	4000 pcs./Reel

Product specifications in this catalog are as of Jan.26,2013,and are subject to change or obsolescence without notice. Please consult the approval sheet before ordering.

Please read rating and !Cautions first.

■ AEC-Q200 Murata Standard Specification and Test Methods

			Specific	cation.	AEC 0200 Test Method				
No	AEC-Q200 T		Temperature Compensating Type	High Dielectric Type				AEC-Q200 Test Meth	od
1	Pre-and Post-Stress Electrical Test				-				
2	High Temperature		The measured and observed characteristics should satisfy the			Set the capacitor for 1000±12 hours at 150±3°C. Set for			
	Exposure (Storage)	_	specifications in the following table.		24±2 hours at room temperature, then measure.				
		Appearance	No marking defects						
		Capacitance	Within ±2.5% or ±0.25pF	C7/R7/L8/R9: Within ±10.0%					
		Change	(Whichever is larger)						
		Q/D.F.	30pFmin. : Q≧1000	C7/R7*/L8 :					
			'	W.V.: 25Vmin.: 0.03 max.					
			30pFmax.: Q ≧400+20C	W.V.: 16V/10V : 0.05 max.					
			C: Nominal Capacitance(pF)	*R7 : W.V.: 100V.: 0.05 max.					
			, ,	R9: 0.075max.					
		I.R.	More than 10,000MΩ or 500Ω •F		t				
			(Whichever is smaller)						
			R9 : More than 150Ω •F						
3	Temperature Cycling	1	The measured and observed character	eristics should satisfy the	Fix the	capac	citor to the sur	oporting jig in the sam	ne manner and under
		,	specifications in the following table.	one and one and outlery and				9). Perform cycle test	
		Appearance	No marking defects		t			e following table. Set	-
		Capacitance	Within ±2.5% or ±0.25pF	C7/R7/L8/R9: Within ±10.0%	t		ature, then me	-	101 24±2 Hours at
		Change	•	67/11//E6/119. WILLIIII ±10.0%	1001111	emper	ature, trien me	easure .	
		Q/D.F.	(Whichever is larger) 30pFmin. : Q≧1000	C7/R7*/L8 :	†	0.	T1: / 1.3	Cvo	les
		U/D.F.	'	W.V.: 25Vmin.: 0.03 max.		Step	Time(min)	1000 (for ΔC/C7/R7)	300 (for 5G/L8/R9)
			30pFmax.: Q ≥400+20C			1	15±3	-55°C+0/-3	-55°C+0/-3
			C. Nomicel Conservation (5)	W.V.: 16V/10V : 0.05 max.		2	1	Room	Room
			C: Nominal Capacitance(pF)	*R7 : W.V.: 100V.: 0.05 max.		3	15±3	125°C+3/-0	150°C+3/-0
		L D	14 11 10 22212	R9: 0.075max.		4	1	Room	Room
		I.R.	More than $10,000M\Omega$ or $500\Omega \cdot F$						
			(Whichever is smaller)						
								igh dielectric constan	• •
								at 150+0/-10 °C for on	e hour and then set
							rs at room tem	•	
					Perfor	m the i	nitial measure	ement.	
_									
4	Destructive	1	No defects or abnormalities		Per El	A-469.			
4	Destructive Phisical Analysis		No defects or abnormalities		Per El	A-469.			
			No defects or abnormalities The measured and observed charact	eristics should satisfy the			-hour heat (25	5 to 65°C) and humidit	y (80 to 98%)
	Phisical Analysis			eristics should satisfy the	Apply	the 24		5 to 65°C) and humidit	y (80 to 98%)
	Phisical Analysis	Appearance	The measured and observed character	eristics should satisfy the	Apply treatm	the 24	own below, 10		
	Phisical Analysis	•	The measured and observed charact specifications in the following table.	eristics should satisfy the C7/R7/L8/R9: Within ±12.5%	Apply treatm	the 24 ent sho	own below, 10	consecutive times. m temperature, then r	neasure. Humidity
	Phisical Analysis	Appearance	The measured and observed charact specifications in the following table. No marking defects	,	Apply treatm Set for Temper	the 24 ent sho	own below, 10 2 hours at room	consecutive times. m temperature, then r Humidity 80~98% Humidity	neasure. Humidity 80~98% Humidity
	Phisical Analysis	Appearance Capacitance	The measured and observed charact specifications in the following table. No marking defects Within ±3.0% or ±0.30pF	,	Apply treatm Set for Temper (°C) 70	the 24 ent sho	own below, 10 hours at roor	consecutive times. m temperature, then r	neasure. Humidity
	Phisical Analysis	Appearance Capacitance Change	The measured and observed charact specifications in the following table. No marking defects Within ±3.0% or ±0.30pF (Whichever is larger)	C7/R7/L8/R9: Within ±12.5%	Apply treatm Set for Temper (°C) 70 65 60	the 24 ent sho	own below, 10 2 hours at room	consecutive times. m temperature, then r Humidity 80~98% Humidity	neasure. Humidity 80~98% Humidity
	Phisical Analysis	Appearance Capacitance Change	The measured and observed charact specifications in the following table. No marking defects Within ±3.0% or ±0.30pF (Whichever is larger) 30pFmin.: Q≥350	C7/R7/L8/R9: Within ±12.5% C7/R7*/L8:	Apply treatm Set for Temper (°C) 70 65 60 55 50	the 24 ent sho	own below, 10 2 hours at room	consecutive times. m temperature, then r Humidity 80~98% Humidity	neasure. Humidity 80~98% Humidity
	Phisical Analysis	Appearance Capacitance Change	The measured and observed charact specifications in the following table. No marking defects Within ±3.0% or ±0.30pF (Whichever is larger) 30pFmin.: Q≥350	C7/R7/L8/R9: Within ±12.5% C7/R7*/L8: W.V.: 25Vmin.: 0.03 max.	Apply treatm Set for Temper (°C) 70 65 60 55 50 45	the 24 ent sho	own below, 10 2 hours at room	consecutive times. m temperature, then r Humidity 80~98% Humidity	neasure. Humidity 80~98% Humidity
	Phisical Analysis	Appearance Capacitance Change	The measured and observed charact specifications in the following table. No marking defects Within ±3.0% or ±0.30pF (Whichever is larger) 30pFmin.: Q≧350 10pF and over, 30pF and below:	C7/R7/L8/R9: Within ±12.5% C7/R7*/L8: W.V.: 25Vmin.: 0.03 max. W.V.: 16V/10V: 0.05 max.	Apply treatm Set for Temper (°C) 70 65 60 55 50 45 40 35	the 24 ent sho	own below, 10 2 hours at room	consecutive times. m temperature, then r Humidity 80~98% Humidity	neasure. Humidity 80~98% Humidity
	Phisical Analysis	Appearance Capacitance Change	The measured and observed charact specifications in the following table. No marking defects Within ±3.0% or ±0.30pF (Whichever is larger) 30pFmin.: Q≥350 10pF and over, 30pF and below: Q≥275+5C/2	C7/R7/L8/R9: Within ±12.5% C7/R7*/L8: W.V.: 25Vmin.: 0.03 max. W.V.: 16V/10V: 0.05 max. *R7: W.V.: 100V.: 0.05 max.	Apply treatm Set for Temper (°C) 70 65 60 55 50 45 40 35 30 25	the 24 ent sho	own below, 10 2 hours at room	consecutive times. m temperature, then r Humidity 80~98% Humidity	neasure. Humidity 80~98% Humidity
	Phisical Analysis	Appearance Capacitance Change	The measured and observed charact specifications in the following table. No marking defects Within ±3.0% or ±0.30pF (Whichever is larger) 30pFmin.: Q≥350 10pF and over, 30pF and below: Q≥275+5C/2 10pFmax.: Q≥200+10C	C7/R7/L8/R9: Within ±12.5% C7/R7*/L8: W.V.: 25Vmin.: 0.03 max. W.V.: 16V/10V: 0.05 max. *R7: W.V.: 100V.: 0.05 max.	Apply treatm Set for C°C) 70 65 60 55 40 35 30 25 20	the 24 ent sho	own below, 10 2 hours at roor Humidity 90~98%	consecutive times. m temperature, then r Humidity 80~98% Humidity	neasure. Humidity 80~98% Humidity
	Phisical Analysis	Appearance Capacitance Change Q/D.F.	The measured and observed charact specifications in the following table. No marking defects Within ±3.0% or ±0.30pF (Whichever is larger) 30pFmin.: Q≥350 10pF and over, 30pF and below: Q≥275+5C/2 10pFmax.: Q≥200+10C C: Nominal Capacitance(pF)	C7/R7/L8/R9: Within ±12.5% C7/R7*/L8: W.V.: 25Vmin.: 0.03 max. W.V.: 16V/10V: 0.05 max. *R7: W.V.: 100V.: 0.05 max.	Apply treatm Set for Temper (°C) 70 65 60 55 50 45 40 35 30 25 20 15 10 5	the 24 ent sho	own below, 10 2 hours at roor Humidity 90~98%	O consecutive times. In temperature, then resulting the second of the s	neasure. Humidity 80~98% Humidity
	Phisical Analysis	Appearance Capacitance Change Q/D.F.	The measured and observed charact specifications in the following table. No marking defects Within ±3.0% or ±0.30pF (Whichever is larger) 30pFmin. : Q≥350 10pF and over, 30pF and below: Q≥275+5C/2 10pFmax.: Q≥200+10C C: Nominal Capacitance(pF) More than 10,000MΩ or 500Ω · F	C7/R7/L8/R9: Within ±12.5% C7/R7*/L8: W.V.: 25Vmin.: 0.03 max. W.V.: 16V/10V: 0.05 max. *R7: W.V.: 100V.: 0.05 max.	Apply treatm Set for Temper (°C) 70 65 50 45 40 35 20 15 10	the 24 ent sho	own below, 10 2 hours at roor Humidity 90~98%	O consecutive times. In temperature, then resulting the second of the s	neasure. Humidity 80~98% Humidity
	Phisical Analysis	Appearance Capacitance Change Q/D.F.	The measured and observed charact specifications in the following table. No marking defects Within ±3.0% or ±0.30pF (Whichever is larger) 30pFmin.: Q≥350 10pF and over, 30pF and below: Q≥275+5C/2 10pFmax.: Q≥200+10C C: Nominal Capacitance(pF) More than 10,000MΩ or 500Ω ⋅F (Whichever is smaller)	C7/R7/L8/R9: Within ±12.5% C7/R7*/L8: W.V.: 25Vmin.: 0.03 max. W.V.: 16V/10V: 0.05 max. *R7: W.V.: 100V.: 0.05 max.	Apply treatm Set for 70 65 60 55 50 45 40 35 30 25 10 5 0 5 0 0 0 0 0 0 0 0 0 0 0 0 0 0 0	the 24 ent sho	own below, 10 2 hours at roor Humidity 90~98%	O consecutive times. In temperature, then in Humidity 80~98% Humidity 90~98%	neasure. Humidity 80~98% Humidity 90~98%
	Phisical Analysis	Appearance Capacitance Change Q/D.F.	The measured and observed charact specifications in the following table. No marking defects Within ±3.0% or ±0.30pF (Whichever is larger) 30pFmin.: Q≥350 10pF and over, 30pF and below: Q≥275+5C/2 10pFmax.: Q≥200+10C C: Nominal Capacitance(pF) More than 10,000MΩ or 500Ω ⋅F (Whichever is smaller)	C7/R7/L8/R9: Within ±12.5% C7/R7*/L8: W.V.: 25Vmin.: 0.03 max. W.V.: 16V/10V: 0.05 max. *R7: W.V.: 100V.: 0.05 max.	Apply treatm Set for Temper (°C) 70 65 60 0 55 50 45 20 15 10 5 0 0 -5	the 24 ± 2 ± 2 ± 2 ± 2 ± 2 ± 2 ± 2 ± 2 ± 2	own below, 10 Phours at room Humidity 90~98%	Oconsecutive times. In temperature, then in Humidity 80~98% Humidity 90~98% Humidity 20~2 °C One cycle 24hours	neasure. Humidity 80~98% Humidity 90~98%
	Phisical Analysis	Appearance Capacitance Change Q/D.F.	The measured and observed charact specifications in the following table. No marking defects Within ±3.0% or ±0.30pF (Whichever is larger) 30pFmin.: Q≥350 10pF and over, 30pF and below: Q≥275+5C/2 10pFmax.: Q≥200+10C C: Nominal Capacitance(pF) More than 10,000MΩ or 500Ω ⋅F (Whichever is smaller)	C7/R7/L8/R9: Within ±12.5% C7/R7*/L8: W.V.: 25Vmin.: 0.03 max. W.V.: 16V/10V: 0.05 max. *R7: W.V.: 100V.: 0.05 max.	Apply treatm Set for Temper (°C) 70 65 60 0 55 50 45 20 15 10 5 0 0 -5	the 24 ± 2 ± 2 ± 2 ± 2 ± 2 ± 2 ± 2 ± 2 ± 2	own below, 10 Phours at room Humidity 90~98%	O consecutive times. In temperature, then in Humidity 80~98% Humidity 90~98%	neasure. Humidity 80~98% Humidity 90~98%
	Phisical Analysis	Appearance Capacitance Change Q/D.F.	The measured and observed charact specifications in the following table. No marking defects Within ±3.0% or ±0.30pF (Whichever is larger) 30pFmin.: Q≥350 10pF and over, 30pF and below: Q≥275+5C/2 10pFmax.: Q≥200+10C C: Nominal Capacitance(pF) More than 10,000MΩ or 500Ω ⋅F (Whichever is smaller)	C7/R7/L8/R9: Within ±12.5% C7/R7*/L8: W.V.: 25Vmin.: 0.03 max. W.V.: 16V/10V: 0.05 max. *R7: W.V.: 100V.: 0.05 max.	Apply treatm Set for Temper (°C) 70 65 60 0 55 50 45 20 15 10 5 0 0 -5	the 24 ± 2 ± 2 ± 2 ± 2 ± 2 ± 2 ± 2 ± 2 ± 2	own below, 10 Phours at room Humidity 90~98%	Oconsecutive times. In temperature, then results to the second of the s	neasure. Humidity 80~98% Humidity 90~98%
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5	Phisical Analysis	Appearance Capacitance Change Q/D.F.	The measured and observed charact specifications in the following table. No marking defects Within ±3.0% or ±0.30pF (Whichever is larger) 30pFmin.: Q≥350 10pF and over, 30pF and below: Q≥275+5C/2 10pFmax.: Q≥200+10C C: Nominal Capacitance(pF) More than 10,000MΩ or 500Ω ⋅F (Whichever is smaller)	C7/R7/L8/R9: Within ±12.5% C7/R7*/L8: W.V.: 25Vmin.: 0.03 max. W.V.: 16V/10V: 0.05 max. *R7: W.V.: 100V.: 0.05 max. R9: 0.075max.	Apply treatm Set for Temper 70 65 50 45 40 35 30 25 00 -5 -10	the 24 tent shift 24 ± 22 ± 22 tent shift	ed voltage and	Oconsecutive times. In temperature, then results to the second of the s	neasure. Humidity 80~99% Humidity 90~98% 50.7 18 19 20 21 22 23 24 6.8kΩ resister)
5	Phisical Analysis Moisture Resistance	Appearance Capacitance Change Q/D.F.	The measured and observed charact specifications in the following table. No marking defects Within ±3.0% or ±0.30pF (Whichever is larger) 30pFmin.: Q≧350 10pF and over, 30pF and below: Q≧275+5C/2 10pFmax.: Q ≧200+10C C: Nominal Capacitance(pF) More than 10,000MΩ or 500Ω ·F (Whichever is smaller) R9: More than 150Ω ·F	C7/R7/L8/R9: Within ±12.5% C7/R7*/L8: W.V.: 25Vmin.: 0.03 max. W.V.: 16V/10V: 0.05 max. *R7: W.V.: 100V.: 0.05 max. R9: 0.075max.	Apply treatm Set for Temper 70 65 50 45 40 35 30 25 10 5 10 Apply at 85±	the 24 ± 2 2 ± 2 2 ± 2 2 ± 2 2 ± 2 2 ± 2 2 ± 2 2 ±	ed voltage and d 80 to 85% h	Oconsecutive times. In temperature, then recommended the second of the	neasure. Humidity 80~99% Humidity 90~98% 50.7 18 19 20 21 22 23 24 6.8kΩ resister) nours.
5	Phisical Analysis Moisture Resistance	Appearance Capacitance Change Q/D.F. I.R.	The measured and observed charact specifications in the following table. No marking defects Within ±3.0% or ±0.30pF (Whichever is larger) 30pFmin.: Q≧350 10pF and over, 30pF and below: Q≧275+5C/2 10pFmax.: Q ≥200+10C C: Nominal Capacitance(pF) More than 10,000MΩ or 500Ω ·F (Whichever is smaller) R9: More than 150Ω ·F The measured and observed charact specifications in the following table. No marking defects	C7/R7/L8/R9: Within ±12.5% C7/R7*/L8: W.V.: 25Vmin.: 0.03 max. W.V.: 16V/10V: 0.05 max. *R7: W.V.: 100V.: 0.05 max. R9: 0.075max.	Apply treatm Set for Temper 70 65 50 45 40 35 30 25 -10 Apply at 85± Remov	the 24±2 24±2 24±2 Init the rat the rat ve and	ed voltage and d 80 to 85% h	Oconsecutive times. In temperature, then result to the second of the se	neasure. Humidity 80~99% Humidity 90~98% 50.7 18 19 20 21 22 23 24 6.8kΩ resister) nours. ture, then measure.
5	Phisical Analysis Moisture Resistance	Appearance Capacitance Change Q/D.F. I.R. Appearance Capacitance	The measured and observed charact specifications in the following table. No marking defects Within ±3.0% or ±0.30pF (Whichever is larger) 30pFmin.: Q≧350 10pF and over, 30pF and below: Q≧275+5C/2 10pFmax.: Q ≥200+10C C: Nominal Capacitance(pF) More than 10,000MΩ or 500Ω ·F (Whichever is smaller) R9: More than 150Ω ·F The measured and observed charact specifications in the following table. No marking defects Within ±3.0% or ±0.30pF	C7/R7/L8/R9: Within ±12.5% C7/R7*/L8: W.V.: 25Vmin.: 0.03 max. W.V.: 16V/10V: 0.05 max. *R7: W.V.: 100V.: 0.05 max. R9: 0.075max.	Apply treatm Set for Temper 70 65 50 45 40 35 30 25 -10 Apply at 85± Remov	the 24±2 24±2 24±2 Init the rat the rat ve and	ed voltage and d 80 to 85% h	Oconsecutive times. In temperature, then recommended the second of the	neasure. Humidity 80~99% Humidity 90~98% 50.7 18 19 20 21 22 23 24 6.8kΩ resister) nours. ture, then measure.
5	Phisical Analysis Moisture Resistance	Appearance Capacitance Change Q/D.F. I.R. Appearance Capacitance Change	The measured and observed charact specifications in the following table. No marking defects Within ±3.0% or ±0.30pF (Whichever is larger) 30pFmin.: Q≧350 10pF and over, 30pF and below: Q≧275+5C/2 10pFmax.: Q ≥200+10C C: Nominal Capacitance(pF) More than 10,000MΩ or 500Ω ·F (Whichever is smaller) R9: More than 150Ω ·F The measured and observed charact specifications in the following table. No marking defects Within ±3.0% or ±0.30pF (Whichever is larger)	C7/R7/L8/R9: Within ±12.5% C7/R7*/L8: W.V.: 25Vmin.: 0.03 max. W.V.: 16V/10V: 0.05 max. *R7: W.V.: 100V.: 0.05 max. R9: 0.075max.	Apply treatm Set for Temper 70 65 50 45 40 35 30 25 -10 Apply at 85± Remov	the 24±2 24±2 24±2 Init the rat the rat ve and	ed voltage and d 80 to 85% h	Oconsecutive times. In temperature, then recommended the second of the	neasure. Humidity 80~99% Humidity 90~98% 50.7 18 19 20 21 22 23 24 6.8kΩ resister) nours. ture, then measure.
5	Phisical Analysis Moisture Resistance	Appearance Capacitance Change Q/D.F. I.R. Appearance Capacitance	The measured and observed charact specifications in the following table. No marking defects Within ±3.0% or ±0.30pF (Whichever is larger) 30pFmin.: Q≧350 10pF and over, 30pF and below: Q≧275+5C/2 10pFmax.: Q ≥200+10C C: Nominal Capacitance(pF) More than 10,000MΩ or 500Ω ·F (Whichever is smaller) R9: More than 150Ω ·F The measured and observed charact specifications in the following table. No marking defects Within ±3.0% or ±0.30pF (Whichever is larger) 30pF and over: Q≧200	C7/R7/L8/R9: Within ±12.5% C7/R7*/L8: W.V.: 25Vmin.: 0.03 max. W.V.: 16V/10V: 0.05 max. *R7: W.V.: 100V.: 0.05 max. R9: 0.075max. eristics should satisfy the C7/R7/L8/R9: Within ±12.5% C7/R7*/L8:	Apply treatm Set for Temper 70 65 50 45 40 35 30 25 -10 Apply at 85± Remov	the 24±2 24±2 24±2 Init the rat the rat ve and	ed voltage and d 80 to 85% h	Oconsecutive times. In temperature, then recommended the second of the	neasure. Humidity 80~99% Humidity 90~98% 50.7 18 19 20 21 22 23 24 6.8kΩ resister) nours. ture, then measure.
5	Phisical Analysis Moisture Resistance	Appearance Capacitance Change Q/D.F. I.R. Appearance Capacitance Change	The measured and observed charact specifications in the following table. No marking defects Within ±3.0% or ±0.30pF (Whichever is larger) 30pFmin.: Q≧350 10pF and over, 30pF and below: Q≧275+5C/2 10pFmax.: Q ≥200+10C C: Nominal Capacitance(pF) More than 10,000MΩ or 500Ω ·F (Whichever is smaller) R9: More than 150Ω ·F The measured and observed charact specifications in the following table. No marking defects Within ±3.0% or ±0.30pF (Whichever is larger)	C7/R7/L8/R9: Within ±12.5% C7/R7*/L8: W.V.: 25Vmin.: 0.03 max. W.V.: 16V/10V: 0.05 max. *R7: W.V.: 100V.: 0.05 max. R9: 0.075max. eristics should satisfy the C7/R7/L8/R9: Within ±12.5% C7/R7*/L8: W.V.: 25Vmin.: 0.035 max.	Apply treatm Set for Temper 70 65 50 45 40 35 30 25 -10 Apply at 85± Remov	the 24±2 24±2 24±2 Init the rat the rat ve and	ed voltage and d 80 to 85% h	Oconsecutive times. In temperature, then recommended the second of the	neasure. Humidity 80~99% Humidity 90~98% 50.7 18 19 20 21 22 23 24 6.8kΩ resister) nours. ture, then measure.
5	Phisical Analysis Moisture Resistance	Appearance Capacitance Change Q/D.F. I.R. Appearance Capacitance Change	The measured and observed charact specifications in the following table. No marking defects Within ±3.0% or ±0.30pF (Whichever is larger) 30pFmin.: Q≥350 10pF and over, 30pF and below: Q≥275+5C/2 10pFmax.: Q≥200+10C C: Nominal Capacitance(pF) More than 10,000MΩ or 500Ω ·F (Whichever is smaller) R9: More than 150Ω ·F The measured and observed charact specifications in the following table. No marking defects Within ±3.0% or ±0.30pF (Whichever is larger) 30pF and over: Q≥200 30pF and below: Q≥100+10C/3	C7/R7/L8/R9: Within ±12.5% C7/R7*/L8: W.V.: 25Vmin.: 0.03 max. W.V.: 16V/10V: 0.05 max. *R7: W.V.: 100V.: 0.05 max. R9: 0.075max. eristics should satisfy the C7/R7/L8/R9: Within ±12.5% C7/R7*/L8: W.V.: 25Vmin.: 0.035 max. W.V.: 16V/10V: 0.05 max.	Apply treatm Set for Temper 70 65 60 55 50 45 40 35 30 0 -5 -10 Apply at 85± Remov	the 24±2 24±2 24±2 Init the rat the rat ve and	ed voltage and d 80 to 85% h	Oconsecutive times. In temperature, then recommended the second of the	neasure. Humidity 80~99% Humidity 90~98% 50.7 18 19 20 21 22 23 24 6.8kΩ resister) nours. ture, then measure.
5	Phisical Analysis Moisture Resistance	Appearance Capacitance Change Q/D.F. I.R. Appearance Capacitance Change	The measured and observed charact specifications in the following table. No marking defects Within ±3.0% or ±0.30pF (Whichever is larger) 30pFmin.: Q≧350 10pF and over, 30pF and below: Q≧275+5C/2 10pFmax.: Q ≥200+10C C: Nominal Capacitance(pF) More than 10,000MΩ or 500Ω ·F (Whichever is smaller) R9: More than 150Ω ·F The measured and observed charact specifications in the following table. No marking defects Within ±3.0% or ±0.30pF (Whichever is larger) 30pF and over: Q≧200	C7/R7/L8/R9: Within ±12.5% C7/R7*/L8: W.V.: 25Vmin.: 0.03 max. W.V.: 16V/10V: 0.05 max. *R7: W.V.: 100V.: 0.05 max. R9: 0.075max. eristics should satisfy the C7/R7/L8/R9: Within ±12.5% C7/R7*/L8: W.V.: 25Vmin.: 0.035 max. W.V.: 16V/10V: 0.05 max. *R7: W.V.: 100V.: 0.05 max.	Apply treatm Set for Temper 70 65 60 55 50 45 40 35 30 0 -5 -10 Apply at 85± Remov	the 24±2 24±2 24±2 Init the rat the rat ve and	ed voltage and d 80 to 85% h	Oconsecutive times. In temperature, then recommended the second of the	neasure. Humidity 80~99% Humidity 90~98% 50.7 18 19 20 21 22 23 24 6.8kΩ resister) nours. ture, then measure.
5	Phisical Analysis Moisture Resistance	Appearance Capacitance Change Q/D.F. I.R. Appearance Capacitance Change Q/D.F.	The measured and observed charact specifications in the following table. No marking defects Within ±3.0% or ±0.30pF (Whichever is larger) 30pFmin.: Q≥350 10pF and over, 30pF and below: Q≥275+5C/2 10pFmax.: Q≥200+10C C: Nominal Capacitance(pF) More than 10,000MΩ or 500Ω ·F (Whichever is smaller) R9: More than 150Ω ·F The measured and observed charact specifications in the following table. No marking defects Within ±3.0% or ±0.30pF (Whichever is larger) 30pF and over: Q≥200 30pF and below: Q≥100+10C/3 C: Nominal Capacitance(pF)	C7/R7/L8/R9: Within ±12.5% C7/R7*/L8: W.V.: 25Vmin.: 0.03 max. W.V.: 16V/10V: 0.05 max. *R7: W.V.: 100V.: 0.05 max. R9: 0.075max. eristics should satisfy the C7/R7/L8/R9: Within ±12.5% C7/R7*/L8: W.V.: 25Vmin.: 0.035 max. W.V.: 16V/10V: 0.05 max.	Apply treatm Set for Temper 70 65 60 55 50 45 40 35 30 0 -5 -10 Apply at 85± Remov	the 24±2 24±2 24±2 Init the rat the rat ve and	ed voltage and d 80 to 85% h	Oconsecutive times. In temperature, then recommended the second of the	neasure. Humidity 80~99% Humidity 90~98% 50.7 18 19 20 21 22 23 24 6.8kΩ resister) nours. ture, then measure.
5	Phisical Analysis Moisture Resistance	Appearance Capacitance Change Q/D.F. I.R. Appearance Capacitance Change	The measured and observed charact specifications in the following table. No marking defects Within ±3.0% or ±0.30pF (Whichever is larger) 30pFmin.: Q≥350 10pF and over, 30pF and below: Q≥275+5C/2 10pFmax.: Q≥200+10C C: Nominal Capacitance(pF) More than 10,000MΩ or 500Ω ·F (Whichever is smaller) R9: More than 150Ω ·F The measured and observed charact specifications in the following table. No marking defects Within ±3.0% or ±0.30pF (Whichever is larger) 30pF and over: Q≥200 30pF and below: Q≥100+10C/3 C: Nominal Capacitance(pF) More than 1,000MΩ or 50Ω ·F	C7/R7/L8/R9: Within ±12.5% C7/R7*/L8: W.V.: 25Vmin.: 0.03 max. W.V.: 16V/10V: 0.05 max. *R7: W.V.: 100V.: 0.05 max. R9: 0.075max. eristics should satisfy the C7/R7/L8/R9: Within ±12.5% C7/R7*/L8: W.V.: 25Vmin.: 0.035 max. W.V.: 16V/10V: 0.05 max. *R7: W.V.: 100V.: 0.05 max.	Apply treatm Set for Temper 70 65 60 55 50 45 40 35 30 0 -5 -10 Apply at 85± Remov	the 24±2 24±2 24±2 Init the rat the rat ve and	ed voltage and d 80 to 85% h	Oconsecutive times. In temperature, then recommended the second of the	neasure. Humidity 80~99% Humidity 90~98% 50.7 18 19 20 21 22 23 24 6.8kΩ resister) nours. ture, then measure.
5	Phisical Analysis Moisture Resistance	Appearance Capacitance Change Q/D.F. I.R. Appearance Capacitance Change Q/D.F.	The measured and observed charact specifications in the following table. No marking defects Within ±3.0% or ±0.30pF (Whichever is larger) 30pFmin.: Q≥350 10pF and over, 30pF and below: Q≥275+5C/2 10pFmax.: Q≥200+10C C: Nominal Capacitance(pF) More than 10,000MΩ or 500Ω ·F (Whichever is smaller) R9: More than 150Ω ·F The measured and observed charact specifications in the following table. No marking defects Within ±3.0% or ±0.30pF (Whichever is larger) 30pF and over: Q≥200 30pF and below: Q≥100+10C/3 C: Nominal Capacitance(pF)	C7/R7/L8/R9: Within ±12.5% C7/R7*/L8: W.V.: 25Vmin.: 0.03 max. W.V.: 16V/10V: 0.05 max. *R7: W.V.: 100V.: 0.05 max. R9: 0.075max. eristics should satisfy the C7/R7/L8/R9: Within ±12.5% C7/R7*/L8: W.V.: 25Vmin.: 0.035 max. W.V.: 16V/10V: 0.05 max. *R7: W.V.: 100V.: 0.05 max.	Apply treatm Set for Temper 70 65 60 55 50 45 40 35 30 0 5 -10 Apply at 85± Remov	the 24±2 24±2 24±2 Init the rat the rat ve and	ed voltage and d 80 to 85% h	Oconsecutive times. In temperature, then recommended the second of the	neasure. Humidity 80~99% Humidity 90~98% 50.7 18 19 20 21 22 23 24 6.8kΩ resister) nours. ture, then measure.

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■ AEC-Q200 Murata Standard Specification and Test Methods

			Spec	ification.		
No	AEC-Q20	00 Test Item	Temperature Compensating Type	High Dielectric Type	AEC-Q200 Test Method	
7	Operational Life	е	The measured and observed chara	·	Apply 150% of the rated voltage for 1000 ± 12 hours at $125\pm3^{\circ}$ C(for	
			specifications in the following table		Δ C/C7/R7), 150±3°C(for 5G/L8/R9).	
		Appearance	No marking defects	07/D7/L0/D0: With::- 140.50/	Set for 24±2 hours at room temperature, then measure.	
		Capacitance	Within ±3.0% or ±0.30pF (Whichever is larger)	C7/R7/L8/R9: Within ±12.5%	The charge/discharge current is less than 50mA.	
		Change Q/D.F.	30pFmin. : Q≧350	C7/R7*/L8 :	Initial measurement for high dielectric constant type.	
		Q/D.F.	30pFIIIII Q≦330	W.V.: 25Vmin.: 0.035 max.	initial measurement for high defecting constant type.	
			10pF and over, 30pF and below: Q≥275+5C/2	(GCM155R71H 562-223: 0.05max.) (GCM188L81E224: 0.04max.)	Apply 150% of the rated DC voltage for one hour at the maximun	
			10pFmax.: Q ≧200+10C	W.V.: 16V/10V : 0.05 max.	operating temperature ±3°C. Remove and set for 24±2 hours at	
			C: Nominal Capacitance(pF)	*R7 : W.V.: 100V.: 0.05 max.	room temperature. Perform initial measurement.	
		I.R.	More than 1,000M Ω or 50 Ω •F	R9: 0.075max.		
			(Whichever is smaller)			
8	External Visual		No defects or abnormalities		Visual inspection	
9	Phisical Dimen	sion	Within the specified dimensions		Using calipers	
10	Resistance to	Appearance	No marking defects		Per MIL-STD-202 Method 215	
	Solvents	Capacitance	Within the specified tolerance		Solvent 1 : 1 part (by volume) of isopropyl alcohol	
		Change	,		3 parts (by volume) of mineral spirits	
		Q/D.F.	30pFmin. : Q≧1000	C7/R7*/L8:	Solvent 2 : Terpene defluxer	
			'	W.V.: 25Vmin.: 0.025 max.	Solvent 3: 42 parts (by volume) of water	
			30pFmax.: Q ≧400+20C	W.V.: 16V/10V : 0.035 max.	1part (by volume) of propylene glycol monomethylether	
			C: Nominal Capacitance(pF)	*R7 : W.V.: 100V.: 0.05 max. R9 : 0.05max.	1 part (by volume) of monoethanolomine	
		I.R.	More than 10,000MΩ or 500Ω • F	The Following A.		
			(Whichever is smaller)			
11	Mechanical	Appearance	No marking defects		Three shocks in each direction should be applied along 3 mutually	
	Shock	11			perpendicular axes of the test specimen (18 shocks).	
	SHOCK	Change	within the specified tolerance		The specified test pulse should be Half-sine and should have a	
		Q/D.F.	30pFmin. : Q≧1000	C7/R7*/L8 :	duration :0.5ms, peak value:1500g and velocity change: 4.7m/s.	
			0 > 100 000	W.V.: 25Vmin.: 0.025 max.		
			30pFmax.: Q ≧400+20C	W.V.: 16V/10V : 0.035 max.		
			C: Nominal Capacitance(pF)	*R7 : W.V.: 100V.: 0.05 max. R9 : 0.05max.		
		I.R.	More than 10.000MΩ or 500Ω ·F	110 : 0.00max.		
			(Whichever is smaller)		Solder the capacitor to the test jig (glass epoxy board) in the same	
2	Vibration	Appearance	No defects or abnormalities			
-	violation.	Capacitance	Within the specified tolerance		manner and under the same conditions as (19). The capacitor	
		Change			should be subjected to a simple harmonic motion having a total	
		Q/D.F.	30pFmin. : Q≧1000	C7/R7*/L8 :	amplitude of 1.5mm, the frequency being varied uniformly between	
				W.V.: 25Vmin.: 0.025 max.	the approximate limits of 10 and 2000Hz. The frequency range, from	
			30pFmax.: Q ≧400+20C	W.V.: 16V/10V : 0.035 max.	10 to 2000Hz and return to 10Hz, should be traversed in	
	1		C: Nominal Capacitance(pF)	*R7 : W.V.: 100V.: 0.05 max.	approximately 20 minutes. This motion should be applied for 12	
				B9: 0.05max.	items in each 3 mutually perpendicular directions (total of 36 times)	
		I.R.	More than 10 000MO or 5000 • F	R9:0.05max.	items in each 3 mutually perpendicular directions (total of 36 times).	
		I.R.	More than $10,000M\Omega$ or 500Ω ·F (Whichever is smaller)	R9:0.05max.	items in each 3 mutually perpendicular directions (total of 36 times).	
13	Resistance to	I.R.	· ·			
13	Resistance to Soldering Heat		(Whichever is smaller)	cteristics should satisfy the	items in each 3 mutually perpendicular directions (total of 36 times). $Immerse \ the \ capacitor \ in \ a \ eutectic \ solder \ solution \ at \ 260\pm5^{\circ}C \ for \\ 10\pm1 \ seconds. \ Set \ at \ room \ temperature \ for \ 24\pm2 \ hours, \ then$	
3			(Whichever is smaller) The measured and observed chara	cteristics should satisfy the	Immerse the capacitor in a eutectic solder solution at 260±5°C for	
3			(Whichever is smaller) The measured and observed chara specifications in the following table	cteristics should satisfy the	Immerse the capacitor in a eutectic solder solution at $260\pm5^{\circ}$ C for 10 ± 1 seconds. Set at room temperature for 24 ± 2 hours, then	
13		Appearance	(Whichever is smaller) The measured and observed chara specifications in the following table No marking defects	cteristics should satisfy the	Immerse the capacitor in a eutectic solder solution at $260\pm5^{\circ}$ C for 10 ± 1 seconds. Set at room temperature for 24 ± 2 hours, then	
13		Appearance Capacitance	(Whichever is smaller) The measured and observed chara specifications in the following table No marking defects	cteristics should satisfy the	Immerse the capacitor in a eutectic solder solution at 260±5°C for 10±1 seconds. Set at room temperature for 24±2 hours, then measure. Initial measurement for high dielectric constant type Perform a heat treatment at 150+0/-10 °C for one hour and then set	
13		Appearance Capacitance Change	(Whichever is smaller) The measured and observed chara specifications in the following table No marking defects Within the specified tolerance	C7/R7*/L8 : W.V.: 25Vmin.: 0.025 max. W.V.: 16V/10V : 0.035 max. *R7 : W.V.: 100V.: 0.05 max.	Immerse the capacitor in a eutectic solder solution at 260±5°C for 10±1 seconds. Set at room temperature for 24±2 hours, then measure. Initial measurement for high dielectric constant type	
13		Appearance Capacitance Change Q/D.F.	(Whichever is smaller) The measured and observed chara specifications in the following table No marking defects Within the specified tolerance 30pFmin. : Q≥1000 30pFmax.: Q≥400+20C C: Nominal Capacitance(pF)	C7/R7*/L8: W.V.: 25Vmin.: 0.025 max. W.V.: 16V/10V: 0.035 max.	Immerse the capacitor in a eutectic solder solution at 260±5°C for 10±1 seconds. Set at room temperature for 24±2 hours, then measure. Initial measurement for high dielectric constant type Perform a heat treatment at 150+0/-10 °C for one hour and then set for 24±2 hours at room temperature.	
13		Appearance Capacitance Change	(Whichever is smaller) The measured and observed chara specifications in the following table No marking defects Within the specified tolerance 30pFmin. : Q≥1000 30pFmax.: Q≥400+20C	C7/R7*/L8 : W.V.: 25Vmin.: 0.025 max. W.V.: 16V/10V : 0.035 max. *R7 : W.V.: 100V.: 0.05 max.	Immerse the capacitor in a eutectic solder solution at 260±5°C for 10±1 seconds. Set at room temperature for 24±2 hours, then measure. Initial measurement for high dielectric constant type Perform a heat treatment at 150+0/-10 °C for one hour and then set for 24±2 hours at room temperature.	

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■AEC-Q200 Murata Standard Specification and Test Methods

lo AEC-	Q200 Test Item		ecification.			AEC-Q200 Te	est Method
14 Thermal S		Temperature Compensating Type The measured and observed charac	High Dielectric Type	Ein al			
14 Thermal S		specifications in the following table.	teristics should satisfy the	the same	Fix the capacitor to the supporting jig in the same manner at the same conditions as (19). Perform the 300 cycles according		ne 300 cycles according to
	Appearance	No marking defects	T	the two heat treatments listed in the following table(Maximum			
	Capacitance Change	Within ±2.5% or ±0.25pF (Whichever is larger)	C7/R7/L8/R9: Within ±10.0%	transfer time is 20 seconds). Set for 24±2 hours at room temperature, then measure			
	Q/D.F.	30pFmin. : Q≧1000	C7/R7**/L8: W.V.: 25Vmin.: 0.025 max.*	T			
	Q, 2	30pFmax.: Q ≧400+20C	*0.05max:GCM188R71E/1H563 to 104		Step		2 125+3/-0(forΔC/C7/R7)
		C: Nominal Capacitance(pF)	**R7 : W.V.: 100V.: 0.05 max. W.V.: 16V/10V : 0.035 max.		Temp.(°C)	-55+0/-3	150+3/-0(for 5G/L8/R9)
	I.R.	More than 10,000MΩ or 500Ω • F	R9: 0.05max		(min.)	15±3	15±3
		(Whichever is smaller)		· Initial m	neasuremer	nt for high dielectric	constant type
				Perform a for 24±2	a heat treat hours at roo	ment at 150+0/-10 om temperature.	°C for one hour and then set
5 ESD	Appearance	No marking defects		_	ne initial m -Q200-002	easurement.	
	Capacitance	Within the specified tolerance		- 31 ALO-	3200-00Z		
	Change						
	Q/D.F.	30pFmin. : Q≧1000	C7/R7*/L8 : W.V.: 25Vmin.: 0.025 max.				
		30pFmax.: Q ≧400+20C	W.V.: 16V/10V :0.035 max.				
		C: Nominal Capacitance(pF)	*R7 : W.V.: 100V.: 0.05 max.				
	I.R.	More than 10,000MΩ or 500Ω∙F	R9: 0.05max.	+			
1		(Whichever is smaller)					
6 Solderabili	ty	95% of the terminations is to be solo	lered evenly and continuously.	capaci 5902)	itor in a sol (25% rosin	ution of ethanol(JIS in weight propotio	oreheating, immerse the 6-K-8101) and rosin (JIS-K- n). Immerse in seconds at 235±5°C.
				ethand propot second	ol(JIS-K-810 tion). Immer ds at 235±5	01) and rosin (JIS- rse in eutectic sold °C.	itor in a solution of K-5902) (25% rosin in weight er solution for 5+0/-0.5
				After pethano	oreheating, ol(JIS-K-810	immerse the capac 01) and rosin (JIS- rse in eutectic sold	or 8 hours±15 minutes. sitor in a solution of K-5902) (25% rosin in weight er solution for 120±5
7 Electrical	Appearance	No defects or abnormalities		Visual ins	spection.		
Chatacteri- zation	Capacitance Change	Within the specified tolerance		-		O.F. should be mea ge shown in the tab	sured at 25°C at the lle.
	Q/D.F.	30pFmin.: Q≧1000 30pFmax.: Q≧400+20C C: Nominal Capacitance(pF)	C7/R7*/L8: W.V.: 25Vmin.: 0.025 max. W.V.: 16V/10V:0.035 max. *R7: W.V.: 100V.: 0.05 max. R9: 0.05max.	F	Char. tem requency	Δ C,5G (1000 pF and belo 1±0.1MHz 0.5 to 5Vrms	ΔC,5G (more than 1000pF) C7,R7,L8,R9(C≦10 μ F) 1±0.1kHz 1±0.2Vrms
	I.R. 25°C	More than $100,000M\Omega$ or $1000\Omega \cdot F$ (Whichever is smaller)	More than 10,000MΩ or 500Ω∙F (Whichever is smaller)	exceedin	g the rated		asured with a DC voltage not d 125°C(for Δ C/C7/R7)/ 150°C
	I.R. 125°C	More than 10,000MΩ or 100Ω•F (Whichever is smaller)	More than 1,000M Ω or 10 Ω -F (Whichever is smaller)	(101 504/1	Lo/1 (3/ WILTII	z minutes of clid	aa.
	I.R. 150°C	More than 10,000MΩ or 100Ω•F (Whichever is smaller)	More than 1,000M Ω or 1 Ω -F (Whichever is smaller)				
	Dielectric Strength	No failure		applied b	etween the		0% of the rated voltage is to 5 seconds, provided the 50mA.

■AEC-Q200 Murata Standard Specification and Test Methods

				Specification.	
No	AEC-Q200		Temperature Compensating Type	High Dielectric Type	AEC-Q200 Test Method
18	Board Flex	Appearance	No marking defects		Solder the capacitor on the test jig (glass epoxy board) shown in Fig1 using a eutectic solder. Then apply a force in the direction shown in Fig 2 for 5±1sec. The soldering should be done by the reflow method and should be conducted with care so that the
		Capacitance	Within ±5.0% or ±0.5pF	C7/R7/L8/R9: Within ±10.0%	soldering is uniform and free of defects such as heat shock.
		Change Q/D.F.	(Whichever is larger) 30pFmin. : Q≧1000	C7/R7*/L8 : W.V.: 25Vmin.: 0.025 max.	Type ਤੁੰਮੂ b c
		Q/D.I .	Зорг пшп Ф≦ 1000	W.V.: 16V/10V :0.035 max.	GCM15 0.5 1.5 0.6 GCM18 0.6 2.2 0.9
			30pFmax.: Q ≧400+20C	*R7 : W.V.: 100V.: 0.05 max.	GCM21 0.8 3.0 1.3 GCM31 2.0 4.4. 1.7
			C: Nominal Capacitance(pF)	R9: 0.05max.	GCM31 2.0 4.4 1.7 GCM32 2.0 4.4 2.6
		I.R.	More than 10,000MΩ or 500 (Whichever is smaller)	Ω·F	
			b b c c c c c c c c	t: 1.6mm (GCM15:0.8mm)	Pressur Min mm) ### Pressur Min min speed: 1. Omm/sec Pressurize Pressurize Flexure: ≤2 (High Dielectric Type) Flexure: ≤3 (Temperature Compensating Type)
19	Terminal Strength	Appearance	No marking defects		Solder the capacitor to the test jig (glass epoxy board) shown in Fig.3 using a eutectic solder. Then apply *18N force in parallel with
	Strength	Capacitance	Within specified tolerance		the test jig for 60sec.
		Change Q/D.F.	30pFmin. : Q≧1000	C7/R7*/L8: W.V.: 25Vmin.: 0.025 max.	The soldering should be done either with an iron or using the reflow method and should be conducted with care so that the soldering is
			30pFmax.: Q ≧400+20C	W.V.: 16V/10V :0.035 max. *R7 : W.V.: 100V.: 0.05 max.	uniform and gree of defects such as heat shock
			C: Nominal Capacitance(pF)	R9: 0.05max.	*2N(GCM15) Type a b c
		I.R.	More than $10,000M\Omega$ or 500 (Whichever is smaller)	Ω•+	GCM15 0. 4 1. 5 0. 5
					GCM18 1.0 3.0 1.2 GCM21 1.2 4.0 1.65
					GCM31 2.2 5.0 2.0 GCM32 2.2 5.0 2.9
					(in mm)
			 ラント*	Α.	<u> </u>
			771	ф	
					Solder resist
					Baked electrode or
					Copper foil Fig. 3
20	Beam Load Test		Destruction value should be		Place the capacitor in the beam load fixture as Fig 4.
			< Chip L dimension : 2.5mm Chip thickr	max. > less > 0.5mm rank : 20N	Apply a force. < Chip Length : 2.5mm max. >
			·	ness ≦0.5mm rank : 8N	
			< Chip L dimension : 3.2mm	max. > ess < 1.25mm rank : 15N	V Iron Board
			· ·	ess < 1.25mm rank : 15N ss ≧1.25mm rank : 54.5N	
					< Chip Length : 3.2mm min. >
					Comp Longar Co.Emm min.
					0.6L
					Fig.4
					Speed supplied the Stress Load : 2.5mm / sec.

5

JEMCGS-0474J

			Specification.				
No	AEC-Q2	00 Test Item	Temperature Compensating Type	High Dielectric Type	AEC-Q200 Test Method		
21	Capacitance	Capacitance	Within the specified tolerance.	C7: Within ±22%	The capacitance change should be measured after 5 min. at		
	Temperature	Change	(Table A)	(-55°C to +125°C)	each specified temperature stage.		
	Characteristics			R7: Within ±15%	(1)Temperature Compensating Type		
				(-55°C to +125°C)	The temperature coefficient is determind using the capacitance		
				L8: Within ±15%	measured in step 3 as a reference. When cycling the temperature		
				(-55°C to +125°C)	sequentially from step1 through 5 (Δ C: +25°C to +125°C,		
				Within +15/-40%	5G:+25°C to +150°C other temp. coeffs.:+25°C to +85°C) the		
				(+125°C to +150°C)	capacitance should be within the specified tolerance for the		
				R9 : Within ±15%	temperature coefficient and capacitance change as Table A-1. The		
				(-55°C to +150°C)	capacitance drift is caluculated by dividing the differences		
		_			betweeen the maximum and minimum measured values in the step		
		Temperature	Within the specified tolerance.		1,3 and 5 by the cap value in step 3.		
		Coefficent	pefficent (Table A)		Step Temperature.(°C)		
					1 25±2		
					2 -55±3(for ΔC to C7/R7)		
					3 25±2		
		Capacitance	Within ±0.2% or ±0.05 pF	┪ /	4 125±3 (for ΔC/C7/R7), 150±3 (for 5G/L8),85±3 (for other TC)		
		Drift	(Whichever is larger.)		5 25±2		
			* Not apply to 1X/25V		(2) High Dielectric Constant Type		
					The ranges of capacitance change compared with the above 25°C		
					value over the temperature ranges shown in the table should be		
					within the specified ranges.		
				/	Initial measurement for high dielectric constant type.		
					Perform a heat treatment at 150+0/-10°C for one hour		
				/	and then set for 24±2 hours at room temperature.		
				V	Perform the initial measurement.		

Nominal Values (ppm/°C)

-55

Capacitance Change from 25°C (%)

Table A

Char.

1.Tape Carrier Packaging(Packaging Code:D/E/W/F/L/J/K) 1.1 Minimum Quantity(pcs./reel)

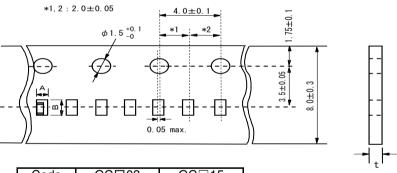
Туре			φ180mm reel		φ330m	ım reel
		Paper	[·] Tape	Plastic Tape	Paper Tape	Plastic Tape
		Code:D/E	Code:W	Code:L	Code:J/ F	Code:K
GC□03		15000(W8P2)	30000(W8P1)		50000(W8P2)	
GC□15		10000(W8P2)	20000(W8P1)		50000(W8P2)	
GC□18		4000			10000	
	6	4000			10000	
GC□21	9	4000			10000	
	В			3000		10000
	6	4000			10000	
GC□31	9	4000			10000	
ВСЦЗТ	M			3000		10000
	С			2000		6000
	9	4000			10000	
GC□32	М			3000		10000
иош 32	Ν			2000		8000
	R/D/E			1000		4000
	М			1000		5000
GC□43	N/R			1000		4000
	E			500		2000
GC□55	М			1000		5000
ССЦ	N/R			1000		4000

1.2 Dimensions of Tape (1)GC□03/15(W8P2 CODE:D/E/J/F)

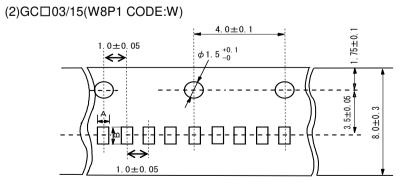
(in:mm)

(in:mm)

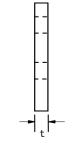
φ1



Code	GC□03	GC□15	
A *3	0.37	0.65	
B *3	0.67	1.15	*3 Nominal value
t	0.5 max.	0.8 max.	

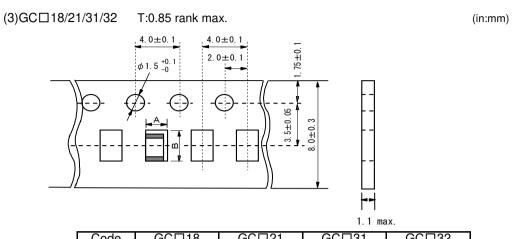


Code	GCI103	G
A *	0.37	0.65
B *	0.67	1.15
t	0.5 max.	0.8 max.

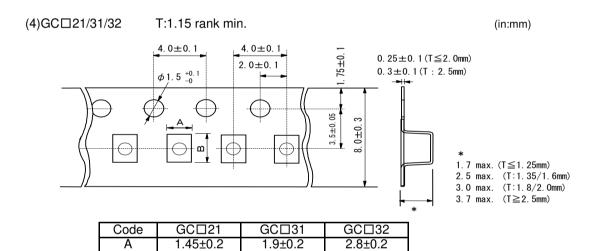


JEMCGP-01894A

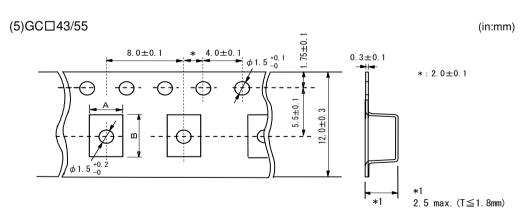
* Nominal value



Code	GC□18	GC□21	GC□31	GC□32
Α	1.05±0.1	1.55±0.15	2.0±0.2	2.8±0.2
В	1.85±0.1	2.3±0.15	3.6±0.2	3.6±0.2



3.5±0.2



3.5±0.2

Code	GC□43	GC□55	
A *2	3.6	5.2	*2 Nominal value
B *2	4.9	6.1]

В

2.25±0.2

状態 単位:

muRata

Package GC□ Type

Fig.1 Package Chips

(in:mm)

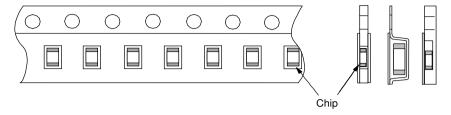


Fig.2 Dimensions of Reel

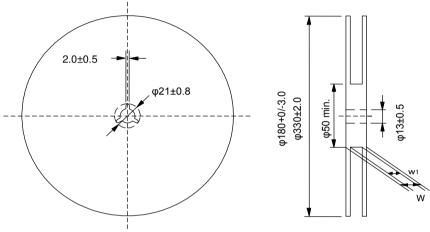
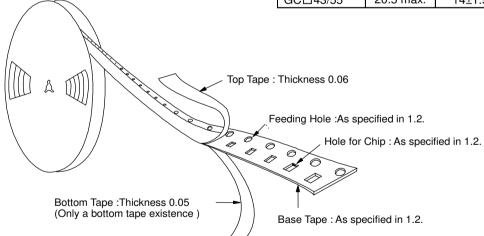


Fig.3 Taping Diagram

	W	W_1
GC□32 max.	16.5 max.	10±1.5
GC□43/55	20.5 max.	14±1.5

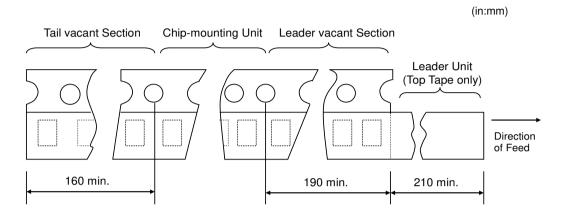


Fップ詰め状態

単位:

- 1.3 Tapes for capacitors are wound clockwise shown in Fig.3.

 (The sprocket holes are to the right as the tape is pulled toward the user.)
- 1.4 Part of the leader and part of the vacant section are attached as follows.



- 1.5 Accumulate pitch : 10 of sprocket holes pitch = 40 ± 0.3 mm
- 1.6 Chip in the tape is enclosed by top tape and bottom tape as shown in Fig.1.
- 1.7 The top tape and base tape are not attached at the end of the tape for a minimum of 5 pitches.
- 1.8 There are no jointing for top tape and bottom tape.
- 1.9 There are no fuzz in the cavity.
- 1.10 Break down force of top tape : 5N min.
 Break down force of bottom tape : 5N min. (Only a bottom tape existence)
- 図 チップ 詰め状態 is made by resin and appeaser and dimens 単位s shown in Fig 2. There are possibly to change the material and dimension due to some impairment.
 - 1.12 Peeling off force: 0.1N to 0.6N* in the direction as shown below.
 - * GC□03:0.05N~0.5N

 165~180°

 Top tape

1.13 Label that show the customer parts number, our parts number, our company name, inspection number and quantity, will be put in outside of reel.

Limitation of use

Please contact our sales representatives or product engineers before using our products for the applications listed below which require of our products for other applications than specified in this product.

- ①Aircraft equipment ②Aerospace equipment ③Undersea equipment ④Power plant control equipment
- 5 Medical equipment 6 Transportation equipment (vehicles, trains, ships, etc.) 7 Traffic signal equipment
- (8) Disaster prevention / crime prevention equipment (9) Data-processing equipment
- (1) Application of similar complexity and/or requirements to the applications listed in the above

■ Fail-safe

Be sure to provide an appropriate fail-safe function on your product to prevent a second damage that may be caused by the abnormal function or the failure of our product.

■ Storage and Operation condition

- 1. The performance of chip monolithic ceramic capacitors may be affected by the storage conditions.
- 1-1. Store capacitors in the following conditions: Temperature of +5°C to +40°C and a Relative Humidity of 20% to 70%.
- (1) Sunlight, dust, rapid temperature changes, corrosive gas atmosphere or high temperature and humidity conditions during storage may affect the solderability and the packaging performance. Please use product within six months of receipt.
- (2) Please confirm solderability before using after six months. Store the capacitors without opening the original bag. Even if the storage period is short, do not exceed the specified atmospheric conditions.
- 1-2. Corrosive gas can react with the termination (external) electrodes or lead wires of capacitors, and result in poor solderability. Do not store the capacitors in an atmosphere consisting of corrosive gas (e.g., hydrogen sulfide, sulfur dioxide, chlorine, ammonia gas etc.).
- 1-3. Due to moisture condensation caused by rapid humidity changes, or the photochemical change caused by direct sunlight on the terminal electrodes and/or the resin/epoxy coatings, the solderability and electrical performance may deteriorate. Do not store capacitors under direct sunlight or in high huimidity conditions

■ Rating

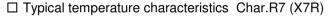
1.Temperature Dependent Characteristics

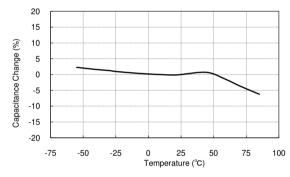
- 1. The electrical characteristics of the capacitor can change with temperature.
- 1-1. For capacitors having larger temperature dependency, the capacitance may change with temperature changes. The following actions are recommended in order to insure suitable capacitance values.
 - (1) Select a suitable capacitance for the operating temperature range.
 - (2) The capacitance may change within the rated temperature.
 - When you use a high dielectric constant type capacitors in a circuit that needs a tight (narrow) capacitance tolerance.

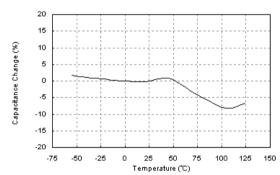
Example: a time constant circuit., please carefully consider the characteristics of these capacitors, such as their aging, voltage, and temperature characteristics.

And check capacitors using your actual appliances at the intended environment and operating conditions.

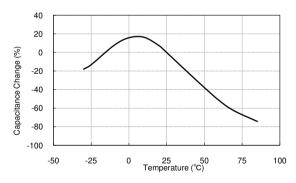
☐ Typical temperature characteristics Char.R6 (X5R)







☐ Typical temperature characteristics Char.F5 (Y5V)



2.Measurement of Capacitance

- 1. Measure capacitance with the voltage and the frequency specified in the product specifications.
- 1-1. The output voltage of the measuring equipment may decrease when capacitance is high occasionally. Please confirm whether a prescribed measured voltage is impressed to the capacitor.
- 1-2. The capacitance values of high dielectric constant type capacitors change depending on the AC voltage applied. Please consider the AC voltage characteristics when selecting a capacitor to be used in a AC circuit.

3. Applied Voltage

- 1. Do not apply a voltage to the capacitor that exceeds the rated voltage as called-out in the specifications.
- 1-1. Applied voltage between the terminals of a capacitor shall be less than or equal to the rated voltage.
- (1) When AC voltage is superimposed on DC voltage, the zero-to-peak voltage shall not exceed the rated DC voltage. When AC voltage or pulse voltage is applied, the peak-to-peak voltage shall not exceed the rated DC voltage.
- (2) Abnormal voltages (surge voltage, static electricity, pulse voltage, etc.) shall not exceed the rated DC voltage.

(E: Maximum possible applied voltage.)

1-2. Influence of overvoltage

Overvoltage that is applied to the capacitor may result in an electrical short circuit caused by the breakdown of the internal dielectric layers .

The time duration until breakdown depends on the applied voltage and the ambient temperature.

4. Applied Voltage and Self-heating Temperature

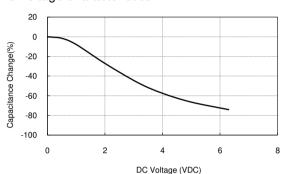
- 1. When the capacitor is used in a high-frequency voltage, pulse voltage, application, be sure to take into account self-heating may be caused by resistant factors of the capacitor.
- 1-1. The load should be contained to the level such that when measuring at atomospheric temperature of 25°C, the product's self-heating remains below 20°C and surface temperature of the capacitor in the actual circuit remains wiyhin the maximum operating temperature.

5. DC Voltage and AC Voltage Characteristic

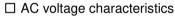
- 1. The capacitance value of a high dielectric constant type capacitor changes depending on the DC voltage applied. Please consider the DC voltage characteristics when a capacitor is selected for use in a DC circuit.
- 1-1. The capacitance of ceramic capacitors may change sharply depending on the applied voltage. (See figure) Please confirm the following in order to secure the capacitance.
- (1) Whether the capacitance change caused by the applied voltage is within the range allowed or not.

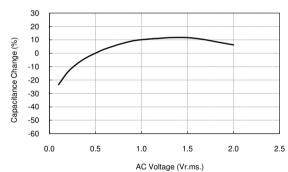
□ DC voltage characteristics

(2) In the DC voltage characteristics, the rate of capacitance change becomes larger as voltage increases. Even if the applied voltage is below the rated voltage. When a high dielectric constant type capacitor is in a circuit that needs a tight (narrow) capacitance tolerance. Example: a time constant circuit., please carefully consider the characteristics of these capacitors, such as their aging, voltage, and temperature characteristics. And check capacitors using your actual appliances at the intended environment and operating conditions.



2. The capacitance values of high dielectric constant type capacitors change depending on the AC voltage applied. Please consider the AC voltage characteristics when selecting a capacitor to be used in a AC circuit.

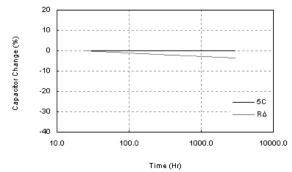




6. Capacitance Aging

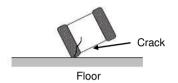
- 1. The high dielectric constant type capacitors have the characteristic in which the capacitance value decreases with the passage of time.
 - When you use a high dielectric constant type capacitors in a circuit that needs a tight (narrow) capacitance tolerance. Example: a time constant circuit., please carefully consider the characteristics of these capacitors, such as their aging, voltage, and temperature characteristics.

And check capacitors using your actual appliances at the intended environment and operating conditions.

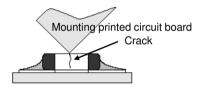


7. Vibration and Shock

- 1. The capacitors mechanical actress (vibration and shock) shall be specified for the use environment. Please confirm the kind of vibration and/or shock, its condition, and any generation of resonance. Please mount the capacitor so as not to generate resonance, and do not allow any impact on the terminals.
- 2. Mechanical shock due to falling may cause damage or a crack in the dielectric material of the capacitor. Do not use a fallen capacitor because the quality and reliability may be deteriorated.



3. When printed circuit boards are piled up or handled, the corners of another printed circuit board should not be allowed to hit the capacitor in order to avoid a crack or other damage to the capacitor.

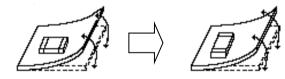


■ Soldering and Mounting

1.Mounting Position

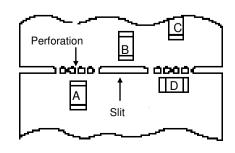
- 1. Confirm the best mounting position and direction that minimizes the stress imposed on the capacitor during flexing or bending the printed circuit board.
- 1-1. Choose a mounting position that minimizes the stress imposed on the chip during flexing or bending of the board.

[Component Direction]



Locate chip horizontal to the direction in which stress acts

[Chip Mounting Close to Board Separation Point]



Chip arrangement Worst A-C-(B~D) Best

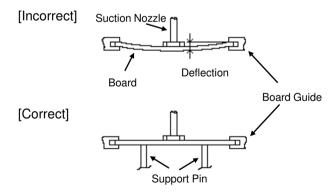
2.Information before mounting

- 1. Do Not re-use capacitors that were removed from the equipment.
- 2. Confirm capacitance characteristics under actual applied voltage.
- 3. Confirm the mechanical stress under actual process and equipment use.
- 4. Confirm the rated capacitance, rated voltage and other electrical characteristics before assembly.
- 5. Prior to use, confirm the Solderability for the capacitors that were in long-term storage.
- 6. Prior to measuring capacitance, carry out a heat treatment for capacitors that were in long-term storage.
- 7. The use of Sn-Zn based solder will deteriorate the reliability of the MLCC.

 Please contact our sales representative or product engineers on the use of Sn-Zn based solder in advance.

3. Maintenance of the Mounting (pick and place) Machine

- 1. Make sure that the following excessive forces are not applied to the capacitors.
- 1-1. In mounting the capacitors on the printed circuit board, any bending force against them shall be kept to a minimum to prevent them from any bending damage or cracking. Please take into account the following precautions and recommendations for use in your process.
- (1) Adjust the lowest position of the pickup nozzle so as not to bend the printed circuit board.
- (2) Adjust the nozzle pressure within a static load of 1N to 3N during mounting.



2.Dirt particles and dust accumulated between the suction nozzle and the cylinder inner wall prevent the nozzle from moving smoothly. This imposes greater force upon the chip during mounting, causing cracked chips. Also the locating claw, when worn out, imposes uneven forces on the chip when positioning, causing cracked chips. The suction nozzle and the locating claw must be maintained, checked and replaced periodically.





4-1.Reflow Soldering

- When sudden heat is applied to the components, the mechanical strength of the components will decrease because a sudden temperature change causes deformation inside the components. In order to prevent mechanical damage to the components, preheating is required for both the components and the PCB board. Preheating conditions are shown in table 1. It is required to keep the temperature differential between the solder and the components surface (ΔT) as small as possible.
- Solderability of Tin plating termination chips might be deteriorated when a low temperature soldering profile where the peak solder temperature is below the melting point of Tin is used. Please confirm the Solderability of Tin plated termination chips before use.
- When components are immersed in solvent after mounting be sure to maintain the temperature difference (ΔT) between the component and the solvent within the range shown in the table 1.

Table 1

Table 1			
Part Number	Temperature Differential		
GC□03/15/18/21/31	ΔΤ≦190°C		
GC□32	ΔΤ≦130°C		

Recommended Conditions

	Pb-Sn	Lead Free Solder	
	Infrared Reflow Vapor Reflow		
Peak Temperature	230~250°C	230~240°C	240~260°C
Atmosphere	Air	Air	Air or N2

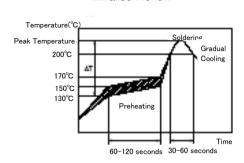
Pb-Sn Solder: Sn-37Pb

Lead Free Solder: Sn-3.0Ag-0.5Cu

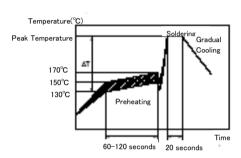
- 4. Optimum Solder Amount for Reflow Soldering
- 4-1. Overly thick application of solder paste results in a excessive solder fillet height. This makes the chip more susceptible to mechanical and thermal stress on the board and may cause the chips to crack.
- 4-2. Too little solder paste results in a lack of adhesive strength on the outer electrode, which may result in chips breaking loose from the PCB.

[Standard Conditions for Reflow Soldering]

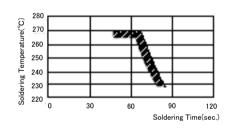
Infrared Reflow



Vapor Reflow



[Allowable Soldering Temperature and Time]



In case of repeated soldering, the accumulated soldering time must be within the range shown above.



* GC □ 03: 1/3 of Chip Thickness min.

in section

4-3. Make sure the solder has been applied smoothly to the end surface to a height of 0.2mm* min.

Inverting the PCB

JEMCGC-2702N

4-2.Flow Soldering

- 1. When sudden heat is applied to the components, the mechanical strength of the components will decrease because a sudden temperature change causes deformation inside the components. In order to prevent mechanical damage in the components, preheating should be required for both of the components and the PCB board. Preheating conditions are shown in table 2. It is required to keep temperature differential between the solder and the components surface (ΔT) as small as possible.
- Excessively long soldering time or high soldering temperature can result in leaching of the outer electrodes, causing poor adhesion or a reduction in capacitance value due to loss of contact between electrodes and end termination.
- 3. When components are immersed in solvent after mounting, be sure to maintain the temperature difference (ΔT) between the component and solvent within the range shown in the table 2.
- 4. Do not apply flow soldering to chips not listed in Table 2.

Table 2

. 4.5.6 =			
Part Number	Temperature Differential		
GC□18/21/31	ΔΤ≦150°C		

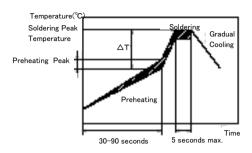
Recommended Conditions

	Pb-Sn Solder	Lead Free Solder
Preheating Peak Temperature	90~110°C	100∼120°C
Soldering Peak Temperature	240~250°C	250~260°C
Atmosphere	Air	N ₂

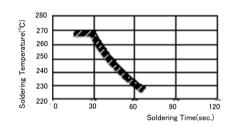
Pb-Sn Solder: Sn-37Pb Lead Free Solder: Sn-3.0Ag-0.5Cu

- Optimum Solder Amount for Flow Soldering
- 5-1. The top of the solder fillet should be lower than the thickness of components. If the solder amount is excessive, the risk of cracking is higher during board bending or any other stressful condition.

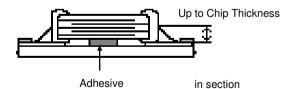
[Standard Conditions for Flow Soldering]



[Allowable Soldering Temperature and Time]



In case of repeated soldering, the accumulated soldering time must be within the range shown above.



4-3. Correction with a Soldering Iron

- 1. When sudden heat is applied to the components when using a soldering iron, the mechanical strength of the components will decrease because the extreme temperature change can cause deformations inside the components. In order to prevent mechanical damage to the components, preheating is required for both the components and the PCB board. Preheating conditions, (The "Temperature of the Soldering Iron tip", "Preheating Temperature", "Temperature Differential" between the iron tip and the components and the PCB), should be within the conditions of table 3. It is required to keep the temperature differential between the soldering Iron and the component surfaces (ΔT) as small as possible.
- 2. After soldering, do not allow the component/PCB to rapidly cool down.
- 3. The operating time for the re-working should be as short as possible. When re-working time is too long, it may cause solder leaching, and that will cause a reduction in the adhesive strength of the terminations.

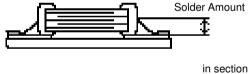
Table 3

Part Number	Temperature of Soldering Iron tip	Preheating Temperature	Temperature Differential (ΔT)	Atmosphere
GC 03/15/18/21/31	350°C max.	150°C min.	ΔT≦190°C	Air
GC□32	280°C max.	150°C min.	ΔT≦130°C	Air

^{*}Applicable for both Pb-Sn and Lead Free Solder Pb-Sn Solder: Sn-37Pb

Lead Free Solder: Sn-3.0Ag-0.5Cu

- 4. Optimum Solder amount when re-working with a Soldering Iron
- 4-1. In case of sizes smaller than 0603, (GC□03/15/18), the top of the solder fillet should be lower than 2/3's of the thickness of the component or 0.5mm whichever is smaller. In case of 0805 and larger sizes, (GC□21/31/32), the top of the solder fillet should be lower than 2/3's of the thickness of the component. If the solder amount is excessive, the risk of cracking is higher during board bending or under any other stressful condition.



- III Section
- 4-2. A Soldering iron with a tip of ø3mm or smaller should be used. It is also necessary to keep the soldering iron from touching the components during the re-work.
- 4-3. Solder wire with Ø0.5mm or smaller is required for soldering.

4-4.Leaded Component Insertion

 If the PCB is flexed when leaded components (such as transformers and ICs) are being mounted, chips may crack and solder joints may break.
 Before mounting leaded components, support the PCB using backup pins or special jigs to prevent warping.

5.Washing

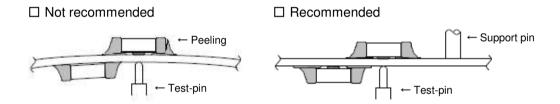
Excessive ultrasonic oscillation during cleaning can cause the PCBs to resonate, resulting in cracked chips or broken solder joints. Take note not to vibrate PCBs.

6.Electrical Test on Printed Circuit Board

- 1. Confirm position of the support pin or specific jig, when inspecting the electrical performance of a capacitor after mounting on the printed circuit board.
- 1-1. Avoid bending printed circuit board by the pressure of a test pin, etc.

 The thrusting force of the test probe can flex the PCB, resulting in cracked chips or open solder joints.

 Provide support pins on the back side of the PCB to prevent warping or flexing.
- 1-2. Avoid vibration of the board by shock when a test pin contacts a printed circuit board.



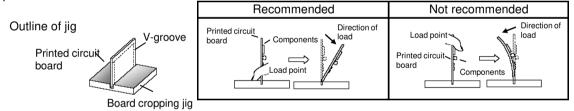
7.Printed Circuit Board Cropping

- 1. After mounting a capacitor on a printed circuit board, do not apply any stress to the capacitor that is caused by bending or twisting the board.
- 1-1. In cropping the board, the stress as shown right may cause the capacitor to crack. Try not to apply this type of stress to a capacitor.



- 2. Check of the cropping method for the printed circuit board in advance.
- 2-1. Printed circuit board cropping shall be carried out by using a jig or an apparatus to prevent the mechanical stress which can occur to the board.
 - (1) Example of a suitable jig

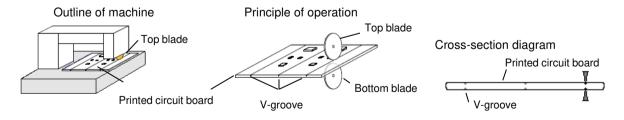
Recommended example: the board should be pushed as close to the near the cropping jig as possible and from the back side of board in order to minimize the compressive stress applied to capacitor. Not recommended example* when the board is pushed at a point far from the cropping jig and from the front side of board as below, the capacitor may form a crack caused by the tensile stress applied to capacitor.

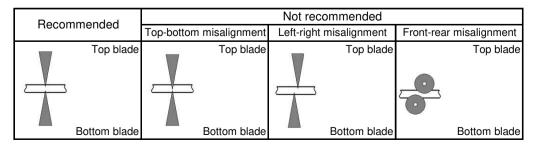


(2) Example of a suitable machine

An outline of a printed circuit board cropping machine is shown as follows. Along the lines with the V-grooves on printed circuit board, the top and bottom blades are aligned to one another when cropping the board.

The misalignment of the position between top and bottom blades may cause the capacitor to crack.





■ Others

1. Under Operation of Equipment

- 1-1. Do not touch a capacitor directly with bare hands during operation in order to avoid the danger of a electric shock.
- 1-2. Do not allow the terminals of a capacitor to come in contact with any conductive objects (short-circuit). Do not expose a capacitor to a conductive liquid, inducing any acid or alkali solutions.
- 1-3. Confirm the environment in which the equipment will operation is under the specified conditions. Do not use the equipment under the following environment.
 - (1) Being spattered with water or oil.
 - (2) Being exposed to direct sunlight.
 - (3) Being exposed to Ozone, ultraviolet rays or radiation.
 - (4) Being exposed to toxic gas (e.g., hydrogen sulfide, sulfur dioxide, chlorine, ammonia gas etc.)
 - (5) Any vibrations or mechanical shocks exceeding the specified limits.
 - (6) Moisture condensing environments.
- 1-4. Use damp proof countermeasures if using under any conditions that can cause condensation.

2. Others

2-1. In an Emergency

- (1) If the equipment should generate smoke, fire or smell, immediately turn off or unplug the equipment. If the equipment is not turned off or unplugged, the hazards may be worsened by supplying continuous power.
- (2) In this type of situation, do not allow face and hands to come in contact with the capacitor or burns may be caused by the capacitors high temperature.

2-2. Disposal of waste

When capacitors are disposed, they must be burned or buried by the industrial waste vender with the appropriate licenses.

2-3. Circuit Design

GC□ Series capacitors in this specification are not safety recognized products.

2-4. Remarks

Failure to follow the cautions may result, worst case, in a short circuit and smoking when the product is used. The above notices are for standard applications and conditions. Contact us when the products are used in special mounting conditions.

Select optimum conditions for operation as they determine the reliability of the product after assembly. The data herein are given in typical values, not guaranteed ratings.

■ Rating

1. Operating Temperature

- 1. The operating temperature limit depends on the capacitor.
- 1-1.Do not apply temperatures exceeding the upper operating temperature.
 - It is necessary to select a capacitor with a suitable rated temperature which will cover the operating temperature range.
 - Also it is necessary to consider the temperature distribution in equipment and the seasonal temperature variable factor.
- 1-2. Consider the self-heating of the capacitor
 - The surface temperature of the capacitor shall be the upper operating temperature or less when including the self-heating factors.

2. Atmosphere surroundings (gaseous and liquid)

- 1. Restriction on the operating environment of capacitors.
- 1-1. The capacitor, when used in the above, unsuitable, operating environments may deteriorate due to the corrosion of the terminations and the penetration of moisture into the capacitor.
- 1-2. The same phenomenon as the above may occur when the electrodes or terminals of the capacitor are subject to moisture condensation.
- 1-3. The deterioration of characteristics and insulation resistance due to the oxidization or corrosion of terminal electrodes may result in breakdown when the capacitor is exposed to corrosive or volatile gases or solvents for long periods of time.

3. Piezo-electric Phenomenon

- 1. When using high dielectric constant type capacitors in AC or pulse circuits, the capacitor itself vibrates at specific frequencies and noise may be generated.
 - Moreover, when the mechanical vibration or shock is added to capacitor, noise may occur.

■ Soldering and Mounting

1.PCB Design

- 1. Notice for Pattern Forms
- 1-1. Unlike leaded components, chip components are susceptible to flexing stresses since they are mounted directly on the substrate.

They are also more sensitive to mechanical and thermal stresses than leaded components. Excess solder fillet height can multiply these stresses and cause chip cracking. When designing substrates, take land patterns and dimensions into consideration to eliminate the possibility of excess solder fillet height.

1-2. It is possible for the chip to crack by the expansion and shrinkage of a metal board.

Please contact us if you want to use our ceramic capacitors on a metal board such as Aluminum.

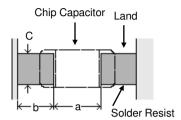
Pattern Forms

Pattern Forms		_
	Prohibited	Correct
Placing Close to Chassis	Chassis Solder (ground) Electrode Pattern	Solder Resist
Placing of Chip Components and Leaded Components	Lead Wire	Solder Resist
Placing of Leaded Components after Chip Component	Soldering Iron Lead Wire	Solder Resist
Lateral Mounting		Solder Resist

2. Land Dimensions

2-1. Chip capacitor can be cracked due to the stress of PCB bending / etc if the land area is larger than needed and has an excess amount of solder.

Please refer to the land dimensions in table 1 for flow soldering, table 2 for reflow soldering.



Please confirm the suitable land dimension by evaluating of the actual SET / PCB.

Table 1 Flow Soldering Method

Table 11 low Soldering Method					
Dimensions Part Number	Chip (L×W)	а	b	С	
GC□18	1.6×0.8	0.6~1.0	0.8~0.9	0.6~0.8	
GC□21	2.0×1.25	1.0~1.2	0.9~1.0	0.8~1.1	
GC□31	3.2×1.6	2.2~2.6	1.0~1.1	1.0~1.4	
				(')	

(in mm)

Table 2 Reflow Soldering Method

Dimensions Part Number	Chip (L×W)	а	b	С
GC□03	0.6×0.3	0.2~0.3	0.2~0.35	0.2~0.4
GC□15	1.0×0.5	0.3~0.5	0.35~0.45	0.4~0.6
GC□18	1.6×0.8	0.6~0.8	0.6~0.7	0.6~0.8
GC□21	2.0×1.25	1.0~1.2	0.6~0.7	0.8~1.1
GC□31	3.2×1.6	2.2~2.4	0.8~0.9	1.0~1.4
GC□32	3.2×2.5	2.0~2.4	1.0~1.2	1.8~2.3

(in mm)